

Pedro LÃ³pez

List of Publications by Year in descending order

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19
papers

166
citations

1307594

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all docs

19
docs citations

19
times ranked

128
citing authors

#	ARTICLE	IF	CITATIONS
1	Extending defect models for Si processing: The role of energy barriers for defect transformation, entropy and coalescence mechanism. Nuclear Instruments & Methods in Physics Research B, 2022, 512, 54-59.	1.4	1
2	Atomistic modeling of laser-related phenomena. , 2021, , 79-136.		0
3	On the anomalous generation of {0â€‰%0â€‰%1} loops during laser annealing of ion-implanted silicon. Nuclear Instruments & Methods in Physics Research B, 2019, 458, 179-183.	1.4	4
4	Identification of Extended Defect Atomic Configurations in Silicon Through Transmission Electron Microscopy Image Simulation. Journal of Electronic Materials, 2018, 47, 4955-4958.	2.2	1
5	I<inf>ON</inf> Degradation in Si Devices in Harsh Radiation Environments: Modeling of Damage-Dopant Interactions. , 2018, , .		2
6	Improved physical models for advanced silicon device processing. Materials Science in Semiconductor Processing, 2017, 62, 62-79.	4.0	5
7	Molecular dynamics simulation of the early stages of self-interstitial clustering in silicon. Materials Science in Semiconductor Processing, 2016, 42, 235-238.	4.0	7
8	Simulation study of ion implanted defects associated to luminescence centers in silicon. , 2011, , .		1
9	Atomistic analysis of B clustering and mobility degradation in highly Bâ€‰doped junctions. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2010, 23, 266-284.	1.9	1
10	Simulation of p-n junctions: Present and future challenges for technologies beyond 32 nm. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, C1A1-C1A6.	1.2	3
11	Improved atomistic damage generation model for binary collision simulations. Journal of Applied Physics, 2009, 105, 083530.	2.5	22
12	Carrier mobility degradation in highly B-doped junctions. , 2009, , .		1
13	Evolution of boron-interstitial clusters in preamorphized silicon without the contribution of end-of-range defects. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 154-155, 247-251.	3.5	7
14	Atomistic analysis of the annealing behavior of amorphous regions in silicon. Journal of Applied Physics, 2007, 101, 093518.	2.5	14
15	Physical insight into boron activation and redistribution during annealing after low-temperature solid phase epitaxial regrowth. Applied Physics Letters, 2006, 88, 191917.	3.3	22
16	Role of silicon interstitials in boron cluster dissolution. Applied Physics Letters, 2005, 86, 031908.	3.3	16
17	Atomistic analysis of the evolution of boron activation during annealing in crystalline and preamorphized silicon. Journal of Applied Physics, 2005, 97, 103520.	2.5	34
18	Atomistic modeling of dopant implantation and annealing in Si: damage evolution, dopant diffusion and activation. Computational Materials Science, 2005, 33, 92-105.	3.0	21

#	ARTICLE	IF	CITATIONS
19	The role of silicon interstitials in the deactivation and reactivation of high concentration boron profiles. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 114-115, 193-197.	3.5	4